

1. Record Nr.	UNINA9910958624203321
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Titolo	RF/microwave circuit design for wireless applications / / Ulrich L. Rohde, Matthias Rudolph
Pubbl/distr/stampa	Hoboken, N.J., : Wiley, 2013
ISBN	1-118-43140-5 1-283-85885-1 1-118-43148-0
Edizione	[2nd ed.]
Descrizione fisica	xix, 893 p. : ill
Altri autori (Persone)	RudolphMatthias <1969->
Disciplina	621.381/32
Soggetti	Microwave circuits - Design and construction Microwave integrated circuits - Computer-aided design Radio frequency integrated circuits - Design and construction Semiconductors - Computer-aided design Wireless communication systems - Equipment and supplies - Design and construction
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di bibliografia	Includes bibliographical references and index.
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